

N-Ch 100V Fast Switching MOSFETs

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC converter
- Portable Equipment
- Power management

General Description:

The UDS55N10 uses super trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

The package form is TO252-3L, which accords with the ROHS standard and Halogen Free standard.

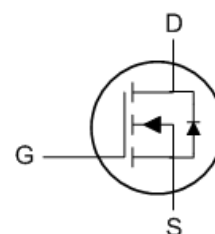
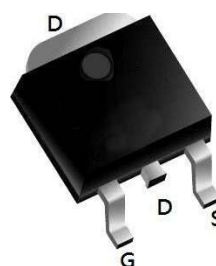
**100% DVDS Tested 100%
Avalanche Tested**

Product Summary



BVDSS	$R_{DS(ON)}$	I_D
100V	14m Ω	55A

TO252-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	55	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	35	A
I_{DM}	Pulsed Drain Current ²	180	A
EAS	Single Pulse Avalanche Energy ³	36	mJ
I_{AS}	Avalanche Current	12	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	38	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	56	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	3.29	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	---	---	V/°C
R _{DS(on)}	Static Drain-Source On-Resistance ²	V _{GS} =10 V, I _D =30A	---	14	18.5	mΩ
		V _{GS} =4.5V, I _D =18A	---	18	24	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.3	1.8	2.3	V
$\Delta V_{GS(th)}$	V _{GS(th)} Temperature Coefficient		---	---	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =100V, V _{GS} =0V, T _J =100°C	---	---	---	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =20A	---	41.2	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.8	---	Ω
Q _g	Total Gate Charge	V _{DS} =50V, V _{GS} =10V, I _D =20A	---	16	---	nC
Q _{gs}	Gate-Source Charge		---	4.6	---	
Q _{gd}	Gate-Drain Charge		---	2.8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, I _D =20A, R _G =3Ω, V _{GS} =10V	---	6	---	ns
T _r	Rise Time		---	28	---	
T _{d(off)}	Turn-Off Delay Time		---	16	---	
T _f	Fall Time		---	7	---	
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	860	---	pF
C _{oss}	Output Capacitance		---	160	---	
C _{rss}	Reverse Transfer Capacitance		---	7	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	55	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =20A, T _J =25°C	---	---	1.4	V
t _{rr}	Reverse Recovery Time	I _F =20A, di/dt=100A / μs,	---	60	---	nS
Q _{rr}	Reverse Recovery Charge	T _J = 25 °C	---	72	---	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=12A, V_{DD}=0V during time in avalanche.
 3. R_{θJA} is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%.

Typical Performance Characteristics

Fig 1: Output Characteristics

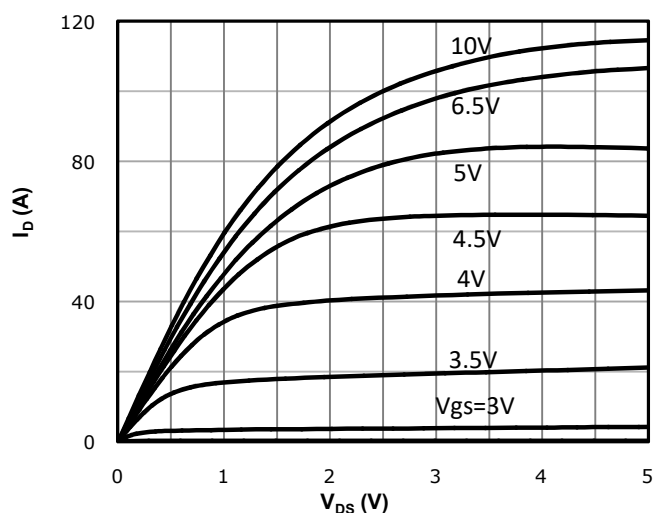


Fig 2: Transfer Characteristics

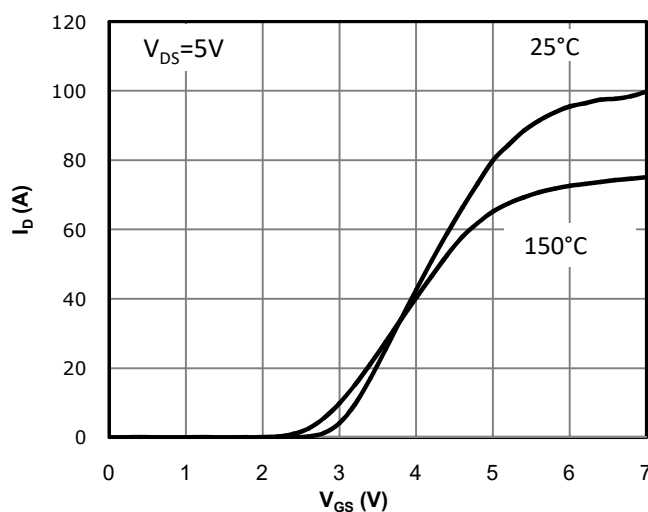


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

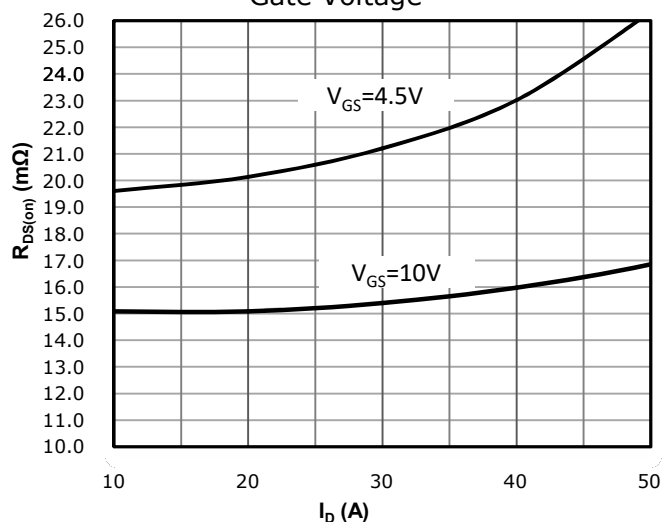


Fig 4: $R_{DS(on)}$ vs Gate Voltage

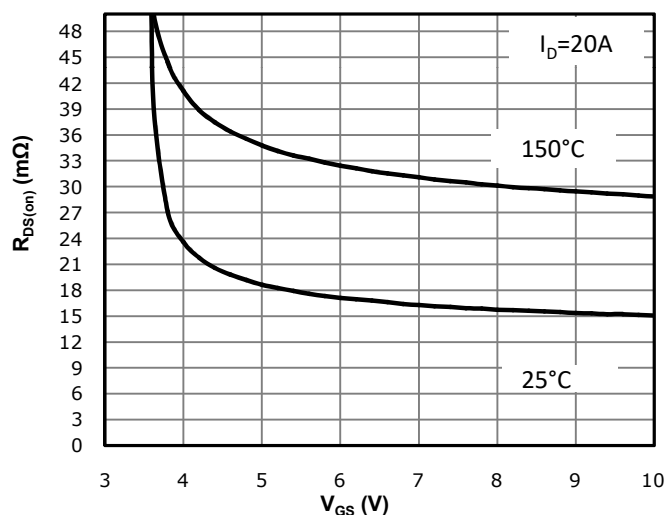


Fig 5: $R_{DS(on)}$ vs. Temperature

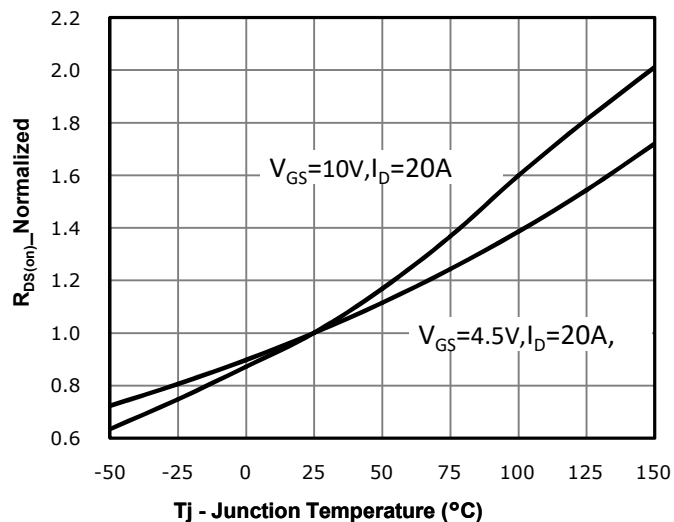


Fig 6: $V_{GS(th)}$ vs. Temperature

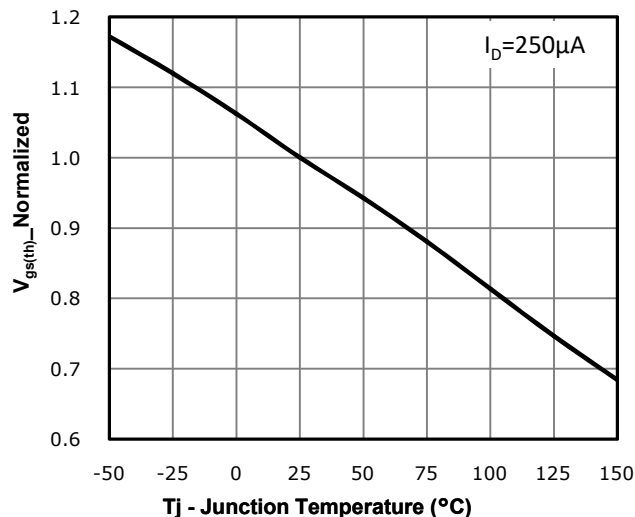


Fig 7: BVdss vs. Temperature

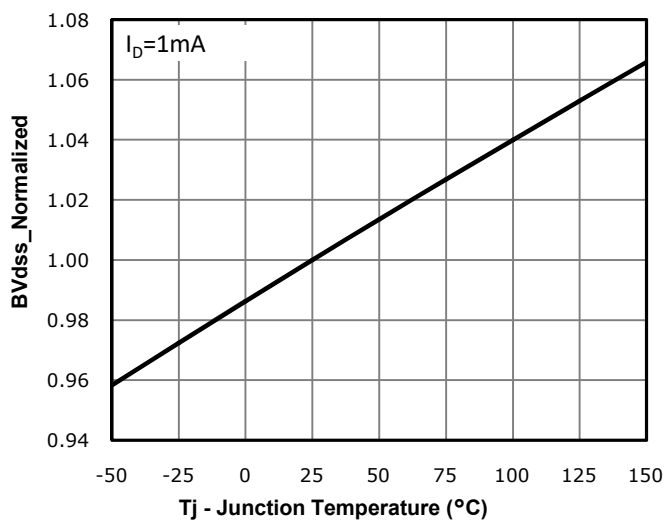


Fig 8: Capacitance Characteristics

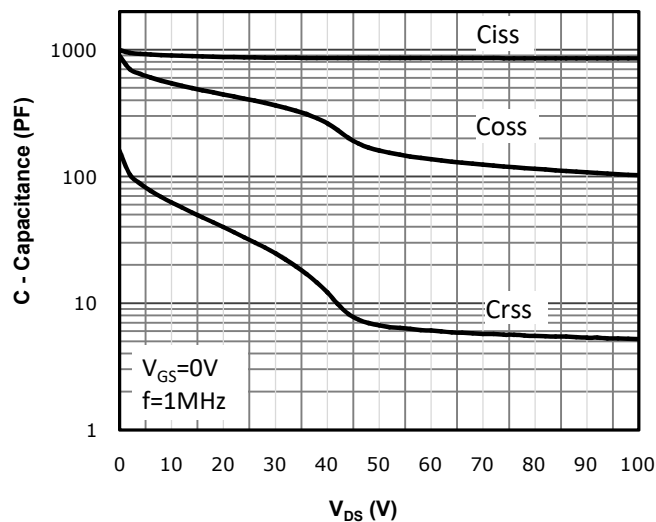


Fig 9: Gate Charge Characteristics

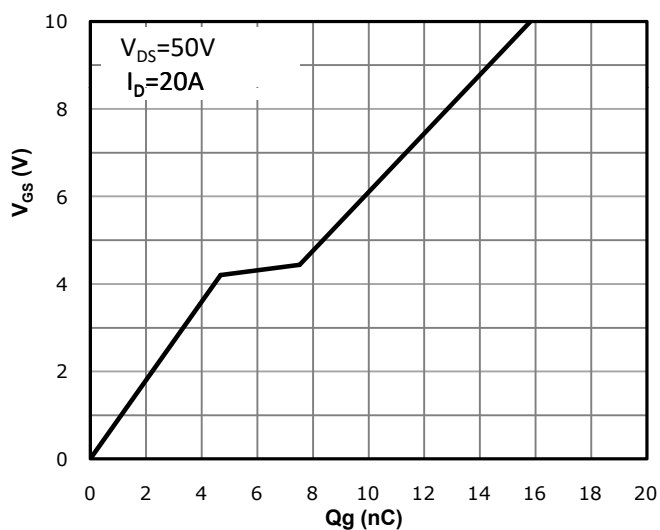


Fig 10: Body-diode Forward Characteristics

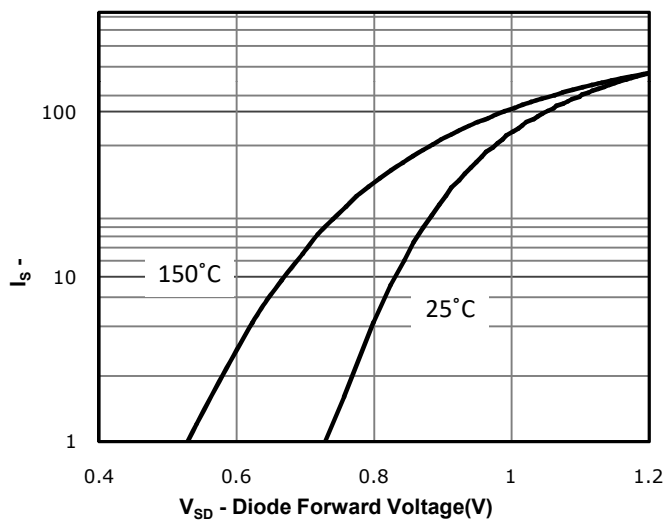


Fig 11: Power Dissipation

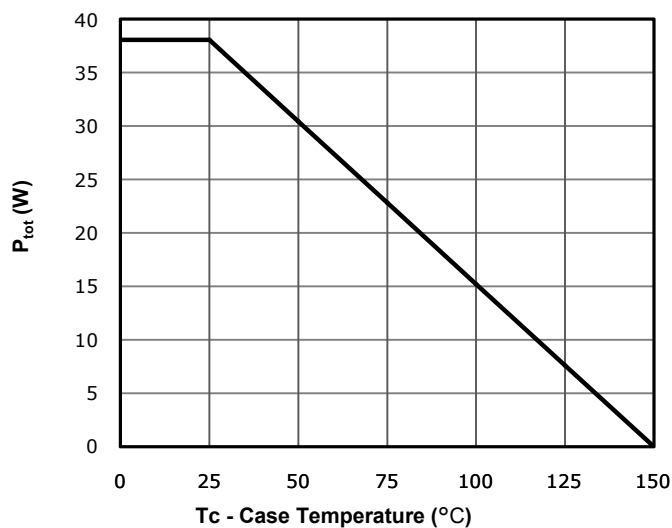
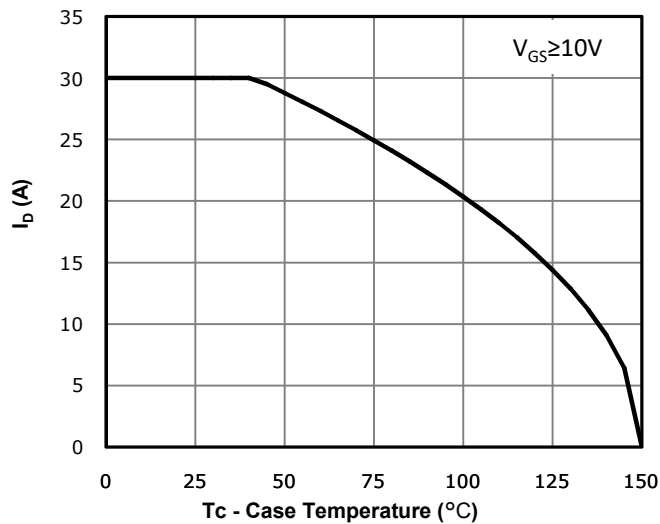
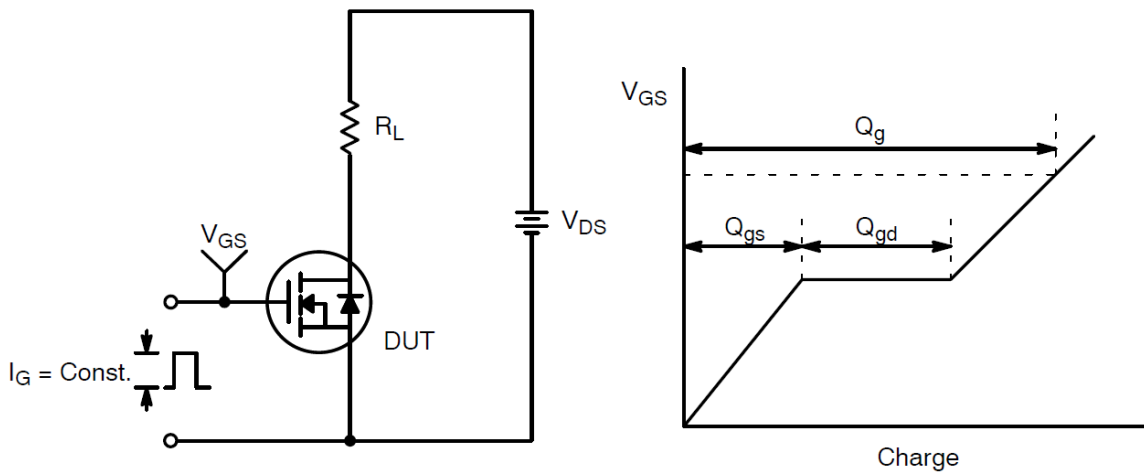


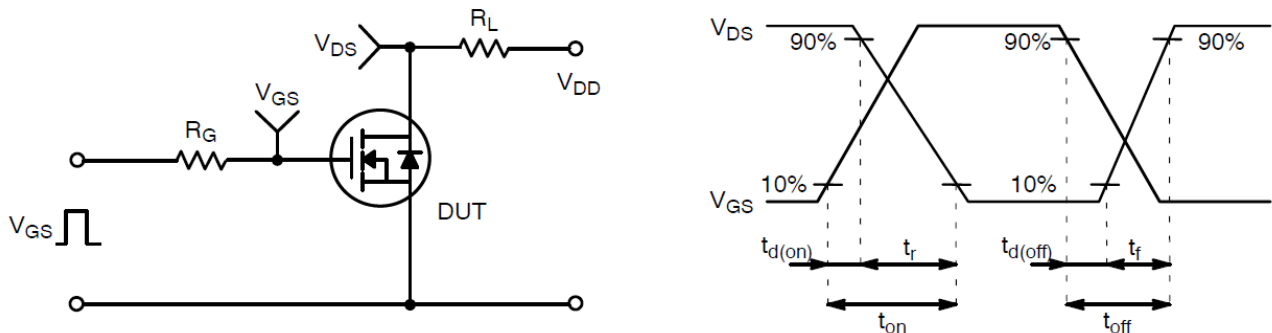
Fig 12: Drain Current Derating



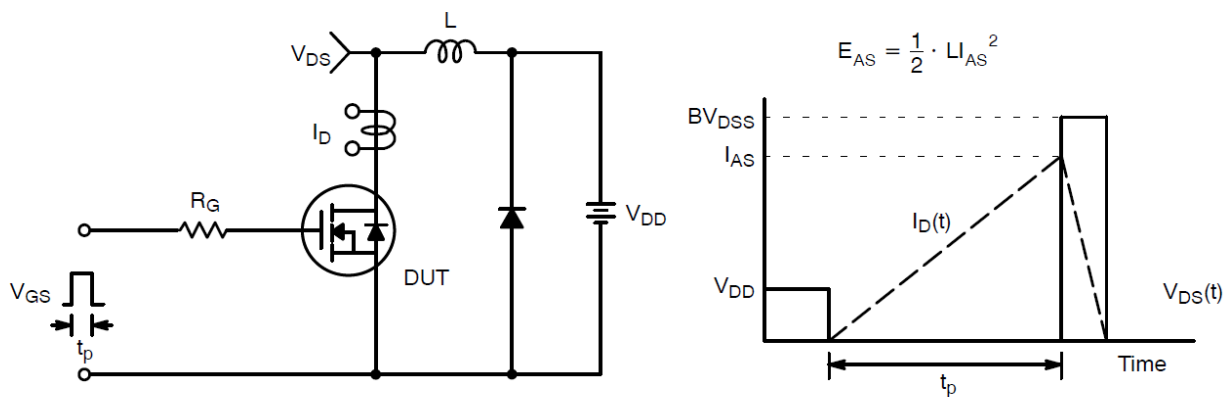
Test Circuit and Waveform:



Gate Charge Test Circuit & Waveform

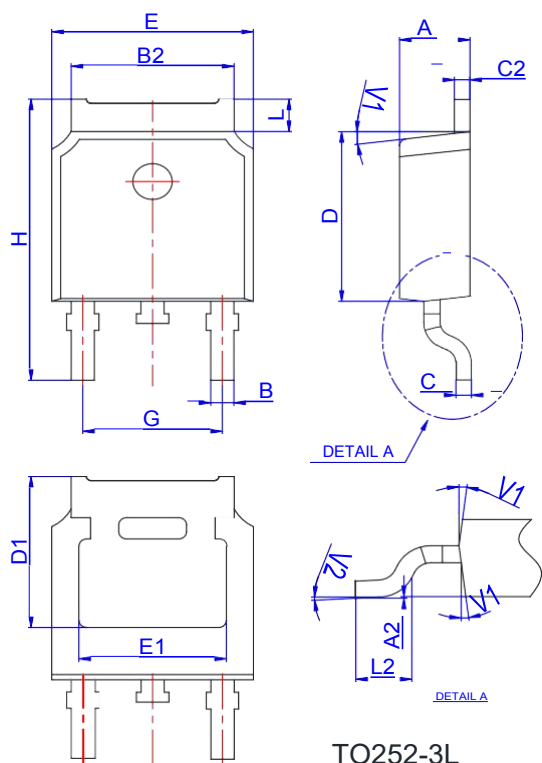


Resistive Switching Test Circuit & Waveforms



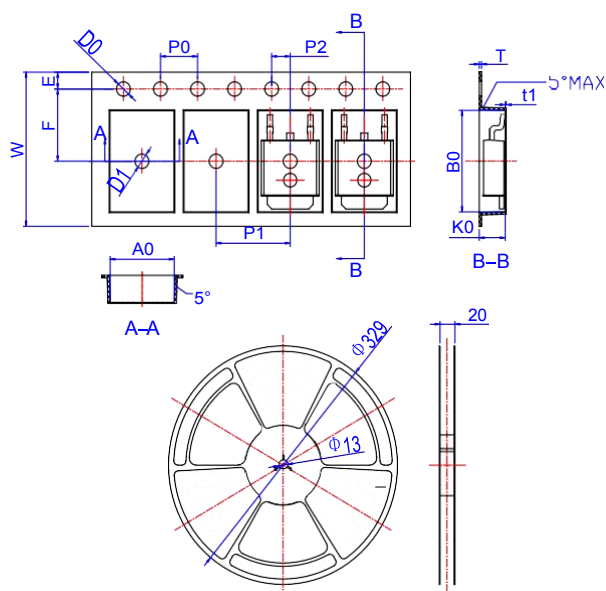
Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Spectification-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583